

Review of: "The third problem is caused by the presence of the dispersant, which spreads when dispersing the nanotubes. Its presence causes confusion in the quantitative detection of the amount of SWCNTs in the sample. In addition, the complexity related to the overlap of the peaks is problematic."

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Because of its very high input impedance, it is very sensitive and is mostly used in induction furnaces to amplify the voltage range, and in general, this type of bipolar transistors (pMOS) is used. It is more for starting high power elements. The most important and almost the only function of bipolar transistors (pMOS) switching The currents are high.

(pMOS) It is a fast transistor in operation, its switching and connecting time is about 1 microsecond.

Because the recovery time in this transistor is very short, as a result, this transistor has good performance at high frequencies.

ome samples have many impurities, such as polyhedral graphite particles, amorphous carbon, and catalyst particles. 3> The optical absorption of these impurities is related to the spectrum, and it is necessary to quantitatively evaluate the removal of background absorption, which in this case is not possible, and quantitative analysis will be accompanied by an error. The third problem is caused by the presence of the dispersant, which spreads when dispersing the nanotubes. Its presence causes confusion in the quantitative detection of the amount of SWCNTs in the sample. In addition, the complexity related to the overlap of the peaks is problematic. a> An estimate of (m,n) in the sample is difficult, and only the data of that the quantitative evaluation of the concentration of the special species of various errors with data analysis.

It causes with unknown frequency along with As a result of the existence of a large number of SWCNTs with different (m,n)

[1][2][3][4][5][6][7][8][9][10][11][12][13][14][15][16][17][18][19][20][21][22][23][24][25][26][27][28][29][30][31][32][33][34][35][36][37][38]



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